

L Number	Hits	Search Text	DB	Time stamp
-	850	(vacuum adj fluorescent adj display vfd).ab,ti,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:41
-	2	((vacuum adj fluorescent adj display vfd).ab,ti,clm.) and (back\$6 diffus\$6) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 17:41
-	5	((vacuum adj fluorescent adj display vfd).ab,ti,clm.) and (back\$6 diffus\$6) adj2 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:00
-	1	2001-540912.NRAN.	DERWENT	2004/04/06 17:43
-	3	("5270613" "5463276" "6340865").PN.	USPAT	2004/04/06 17:46
-	2	4972116.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:00
-	1	4972116.pn.	USPAT	2004/04/06 18:04
-	0	4972116.pn. and back adj electrode same negative	USPAT	2004/04/06 18:04
-	1	4972116.pn. and back adj electrode and negative	USPAT	2004/04/06 18:05
-	1	4972116.pn. and back adj electrode and negative	USPAT	2004/04/06 18:05
-	1	4972116.pn. and back adj electrode and negative	USPAT	2004/04/06 18:09
-	1	5463276.pn.	USPAT	2004/04/06 18:09
-	1	5463276.pn. and ("335" "325")	USPAT	2004/04/06 18:12
-	1	5463276.pn. and ("335" "325" grids negative)	USPAT	2004/04/06 18:12
-	1	5463276.pn. and ("335" "325" grids negative potential bias voltage volt)	USPAT	2004/04/06 18:13
-	1	5463276.pn. and ("335" "325" grids negative potential bias voltage volt "V")	USPAT	2004/04/06 18:13
-	1	5463276.pn. and ("335" "325" negative potential bias voltage volt "V")	USPAT	2004/04/06 18:14
-	1	4719388.pn.	USPAT	2004/04/06 18:19
-	1	4719388.pn. and backing adj electrode with (potential bias voltage volt negative "V")	USPAT	2004/04/06 18:19
-	3	((vacuum adj fluorescent adj display vfd).ab,ti,clm.) and negative near3 respect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:32
-	3	((vacuum adj fluorescent adj display vfd).ab,ti,clm.) and negative near3 respect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:33
-	5643	(vacuum adj fluorescent adj display vfd field adj emission adj (display device)).ab,ti,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:38
-	0	((vacuum adj fluorescent adj display vfd field adj emission adj (display device)).ab,ti,clm.) and negative near4 resepct	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:39
-	54	((vacuum adj fluorescent adj display vfd field adj emission adj (display device)).ab,ti,clm.) and negative near4 respect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 19:07

-	54	((vacuum adj fluorescent adj display vfd field adj emission adj (display device)).ab,ti,clm.) and negative near4 respect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:45
-	2	6682382.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/06 18:45
-	1	6682382.pn.	USPAT	2004/04/06 18:45
-	1	6682382.pn. and (potential bias\$5 voltage volts volt "V" negative positive)	USPAT	2004/04/06 18:46
-	566	negative adj (potential) near4 respect same (voltage volts "V")	USPAT	2004/04/06 19:08
-	566	negative adj (potential) near4 respect same (voltage volts "V")	USPAT	2004/04/06 19:08
-	184	negative adj (potential) near4 respect same (volts "V")	USPAT	2004/04/06 19:20
-	530	negative adj (potential) near4 respect same (positive)	USPAT	2004/04/06 19:20
-	535	negative adj (potential) near4 respect same (positive "+")	USPAT	2004/04/06 19:20
-	471	negative adj (potential) near3 respect same (positive "+")	USPAT	2004/04/06 20:16
-	445	negative adj (potential) adj3 respect same (positive "+")	USPAT	2004/04/06 19:22
-	63	negative adj (potential) adj3 respect same (volt "V")	USPAT	2004/04/06 19:43
-	95	negative adj (bias voltage) adj3 respect same (volt "V")	USPAT	2004/04/06 20:00
-	768	negative adj (potential) adj5 (volts)	USPAT	2004/04/06 20:01
-	32	negative adj (potential) adj5 ("+")	USPAT	2004/04/06 20:05
-	1	4719388.pn.	USPAT	2004/04/06 20:05
-	30	negative adj potential adj4 defin\$6	USPAT	2004/04/06 20:17
-	4	4122376.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/07 10:52
-	1	4122376.pn.	USPAT	2004/04/07 10:52
-	1	4122376.pn. and current	USPAT	2004/04/07 10:52
-	1	4122376.pn. and current	USPAT	2004/04/07 11:06
-	1	4122376.pn. and cathode with (potential voltage bias\$5 volt "V")	USPAT	2004/04/07 11:06
-	527	(313/422).CCLS.	USPAT; US-PGPUB	2004/08/02 14:39
-	59	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter) adj electrode counterelectrode) near7 (potential voltage volt bias)	USPAT; US-PGPUB	2004/08/02 13:57
-	60	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter) adj electrode counterelectrode) near7 (potential voltage volt bias "-"\$4 adj "V")	USPAT; US-PGPUB	2004/08/02 13:59
-	82	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter) adj electrode counterelectrode) near7 (potential voltage volt bias "-"\$4 adj "V")	USPAT; US-PGPUB	2004/08/02 14:20

-	174	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-\$4 adj "V") not ((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter) adj electrode counterelectrode) near7 (potential voltage volt bias "-\$4 adj "V"))	USPAT; US-PGPUB	2004/08/02 14:23
-	97	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-\$4 adj "V") not ((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter) adj electrode counterelectrode) near7 (potential voltage volt bias "-\$4 adj "V"))	USPAT; US-PGPUB	2004/08/02 14:24
-	153	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-\$4 adj "V")	USPAT; US-PGPUB	2004/08/02 14:26
-	1	4988913.pn.	USPAT; US-PGPUB	2004/08/02 14:33
-	66	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5)	USPAT; US-PGPUB	2004/08/02 14:35
-	0	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO) near7 ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam)	USPAT; US-PGPUB	2004/08/02 14:40

-	4	((313/422).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO)	USPAT; US-PGPUB	2004/08/02 14:53
-	2555	((313/422,495-497) or (345/75.2)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 14:52
-	0	("kyungnear2sunear2park.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 14:52
-	1	kyung near2 su near2 park.in.	USPAT; US-PGPUB	2004/08/02 14:52
-	11	((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:03
-	113	((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 15:04

-	102	(((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) not (((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 15:19
-	66	(((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) not (((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO))) and wir\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 15:09

-	2	(((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) not (((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near5 (grid mesh grat\$5) and (indium adj tin adj oxide ITO))) and nesa	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 15:30
-	4	4122376.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 15:30
-	2	4122376.pn.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/02 15:30
-	1	4122376.pn.	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:30
-	1	4122376.pn. and mesh adj shaped	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:31
-	0	4122376.pn. and mesh adj shaped with (potential volt\$6 bias\$5 "V")	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:31
-	1	4122376.pn. and mesh adj shaped same (potential volt\$6 bias\$5 "V")	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:33

-	59	(US-5463276-\$ or US-4280123-\$ or US-4764897-\$ or US-3919558-\$ or US-6630782-\$ or US-6624566-\$ or US-6285121-\$ or US-6278235-\$ or US-5831397-\$ or US-5451835-\$ or US-5440200-\$ or US-5436530-\$ or US-5424605-\$ or US-5272419-\$ or US-5270617-\$ or US-5229691-\$ or US-5202674-\$ or US-5202609-\$ or US-5192892-\$ or US-5189335-\$ or US-5175467-\$ or US-5140230-\$ or US-4980613-\$ or US-4973889-\$ or US-4973888-\$ or US-4972116-\$).did. or (US-4958104-\$ or US-4955681-\$ or US-4939413-\$ or US-4881017-\$ or US-4881005-\$ or US-4853587-\$ or US-4816724-\$ or US-4812716-\$ or US-4748373-\$ or US-4719388-\$ or US-4694225-\$ or US-4651058-\$ or US-4642517-\$ or US-4626899-\$ or US-4622497-\$ or US-4451852-\$ or US-4449148-\$ or US-4417184-\$ or US-4408143-\$ or US-4404493-\$ or US-4356427-\$ or US-4335332-\$ or US-4234815-\$ or US-4227117-\$ or US-4217519-\$ or US-4181871-\$ or US-4167690-\$).did. or (US-4137485-\$ or US-4137478-\$ or US-4118651-\$ or US-5170100-\$).did. or (US-20020047588-\$ or US-20030173888-\$).did.	USPAT; US-PGPUB	2004/08/02 15:33
-	1	(US-2863091-\$).did.	USOCR	2004/08/02 15:33
-	84375	"59" and (grid honeycomb mesh knitted)	USPAT; US-PGPUB; JPO;	2004/08/02 15:34
-	37	((US-5463276-\$ or US-4280123-\$ or US-4764897-\$ or US-3919558-\$ or US-6630782-\$ or US-6624566-\$ or US-6285121-\$ or US-6278235-\$ or US-5831397-\$ or US-5451835-\$ or US-5440200-\$ or US-5436530-\$ or US-5424605-\$ or US-5272419-\$ or US-5270617-\$ or US-5229691-\$ or US-5202674-\$ or US-5202609-\$ or US-5192892-\$ or US-5189335-\$ or US-5175467-\$ or US-5140230-\$ or US-4980613-\$ or US-4973889-\$ or US-4973888-\$ or US-4972116-\$).did. or (US-4958104-\$ or US-4955681-\$ or US-4939413-\$ or US-4881017-\$ or US-4881005-\$ or US-4853587-\$ or US-4816724-\$ or US-4812716-\$ or US-4748373-\$ or US-4719388-\$ or US-4694225-\$ or US-4651058-\$ or US-4642517-\$ or US-4626899-\$ or US-4622497-\$ or US-4451852-\$ or US-4449148-\$ or US-4417184-\$ or US-4408143-\$ or US-4404493-\$ or US-4356427-\$ or US-4335332-\$ or US-4234815-\$ or US-4227117-\$ or US-4217519-\$ or US-4181871-\$ or US-4167690-\$).did. or (US-4137485-\$ or US-4137478-\$ or US-4118651-\$ or US-5170100-\$).did. or (US-20020047588-\$ or US-20030173888-\$).did.) and (grid honeycomb mesh knitted)	IBM_TDB USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:55

-	5	((US-5463276-\$ or US-4280123-\$ or US-4764897-\$ or US-3919558-\$ or US-6630782-\$ or US-6624566-\$ or US-6285121-\$ or US-6278235-\$ or US-5831397-\$ or US-5451835-\$ or US-5440200-\$ or US-5436530-\$ or US-5424605-\$ or US-5272419-\$ or US-5270617-\$ or US-5229691-\$ or US-5202674-\$ or US-5202609-\$ or US-5192892-\$ or US-5189335-\$ or US-5175467-\$ or US-5140230-\$ or US-4980613-\$ or US-4973889-\$ or US-4973888-\$ or US-4972116-\$).did. or (US-4958104-\$ or US-4955681-\$ or US-4939413-\$ or US-4881017-\$ or US-4881005-\$ or US-4853587-\$ or US-4816724-\$ or US-4812716-\$ or US-4748373-\$ or US-4719388-\$ or US-4694225-\$ or US-4651058-\$ or US-4642517-\$ or US-4626899-\$ or US-4622497-\$ or US-4451852-\$ or US-4449148-\$ or US-4417184-\$ or US-4408143-\$ or US-4404493-\$ or US-4356427-\$ or US-4335332-\$ or US-4234815-\$ or US-4227117-\$ or US-4217519-\$ or US-4181871-\$ or US-4167690-\$).did. or (US-4137485-\$ or US-4137478-\$ or US-4118651-\$ or US-5170100-\$).did. or (US-20020047588-\$ or US-20030173888-\$).did.) and (grid honeycomb mesh knitted) and (nesa ito indium adj tin adj oxide)	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 16:12
-	1	5463276.pn.	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:56
-	0	5463276.pn. and (grid mesh) with (potential volt\$6 "V" bias)	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:56
-	0	5463276.pn. and (grid mesh) with (potential volt\$6 "V" bias\$6)	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 15:56
-	1	5463276.pn. and (grid mesh "335" "325")	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 16:32
-	4	((((313/422,495-497) or (345/75.2)).CCLS.) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode beam) near7 (potential voltage volt bias "-"\$4 adj "V") and (cathod\$6) near7 (potential voltage volt bias "-"\$4 adj "V") and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode) near5 (grid mesh grat\$5) and ((back backing scanning scan partition\$5 reflect\$6 rear diffusion focusing isolation counter beam adj control\$6) adj electrode counterelectrode) near5 (transpar\$6 colorless)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:06

-	13	((US-5463276-\$ or US-4280123-\$ or US-4764897-\$ or US-3919558-\$ or US-6630782-\$ or US-6624566-\$ or US-6285121-\$ or US-6278235-\$ or US-5831397-\$ or US-5451835-\$ or US-5440200-\$ or US-5436530-\$ or US-5424605-\$ or US-5272419-\$ or US-5270617-\$ or US-5229691-\$ or US-5202674-\$ or US-5202609-\$ or US-5192892-\$ or US-5189335-\$ or US-5175467-\$ or US-5140230-\$ or US-4980613-\$ or US-4973889-\$ or US-4973888-\$ or US-4972116-\$).did. or (US-4958104-\$ or US-4955681-\$ or US-4939413-\$ or US-4881017-\$ or US-4881005-\$ or US-4853587-\$ or US-4816724-\$ or US-4812716-\$ or US-4748373-\$ or US-4719388-\$ or US-4694225-\$ or US-4651058-\$ or US-4642517-\$ or US-4626899-\$ or US-4622497-\$ or US-4451852-\$ or US-4449148-\$ or US-4417184-\$ or US-4408143-\$ or US-4404493-\$ or US-4356427-\$ or US-4335332-\$ or US-4234815-\$ or US-4227117-\$ or US-4217519-\$ or US-4181871-\$ or US-4167690-\$).did. or (US-4137485-\$ or US-4137478-\$ or US-4118651-\$ or US-5170100-\$).did. or (US-20020047588-\$ or US-20030173888-\$).did.) and (grid honeycomb mesh knitted) and (nesa ito indium adj tin adj oxide transparen\$6 colorless) not (((US-5463276-\$ or US-4280123-\$ or US-4764897-\$ or US-3919558-\$ or US-6630782-\$ or US-6624566-\$ or US-6285121-\$ or US-6278235-\$ or US-5831397-\$ or US-5451835-\$ or US-5440200-\$ or US-5436530-\$ or US-5424605-\$ or US-5272419-\$ or US-5270617-\$ or US-5229691-\$ or US-5202674-\$ or US-5202609-\$ or US-5192892-\$ or US-5189335-\$ or US-5175467-\$ or US-5140230-\$ or US-4980613-\$ or US-4973889-\$ or US-4973888-\$ or US-4972116-\$).did. or (US-4958104-\$ or US-4955681-\$ or US-4939413-\$ or US-4881017-\$ or US-4881005-\$ or US-4853587-\$ or US-4816724-\$ or US-4812716-\$ or US-4748373-\$ or US-4719388-\$ or US-4694225-\$ or US-4651058-\$ or US-4642517-\$ or US-4626899-\$ or US-4622497-\$ or US-4451852-\$ or US-4449148-\$ or US-4417184-\$ or US-4408143-\$ or US-4404493-\$ or US-4356427-\$ or US-4335332-\$ or US-4234815-\$ or US-4227117-\$ or US-4217519-\$ or US-4181871-\$ or US-4167690-\$).did. or (US-4137485-\$ or US-4137478-\$ or US-4118651-\$ or US-5170100-\$).did. or (US-20020047588-\$ or US-20030173888-\$).did.) and (grid honeycomb mesh knitted) and (nesa ito indium adj tin adj oxide))	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 16:32
-	1	5463276.pn.	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 16:32
-	0	5463276.pn. and (grid mesh "335" "325") and (volt\$6 potential "V" bias\$6)	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 16:33
-	1	5463276.pn. and (grid mesh "335" "325")	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 17:53
-	3	("5170100" "4972216" "4881005").pn.	USPAT; US-PGPUB; JPO; IBM_TDB	2004/08/02 17:54
-	0	4972116.pn. and ("10.sub.2")	USPAT; US-PGPUB	2004/08/02 17:59

-	0	4972116.pn. and ("102")	USPAT; US-PGPUB	2004/08/02 17:59
-	1	4972116.pn.	USPAT; US-PGPUB	2004/08/02 17:59
-	1	4972116.pn. and (back adj electrode "10.sub.1" "10.sub.2" "10.sub.3")	USPAT; US-PGPUB	2004/08/02 18:03
-	1	4972116.pn. and (back adj electrode "10.sub.1" "10.sub.2" "10.sub.3" cathode) with (potential volt\$5 "V" bias\$5)	USPAT; US-PGPUB	2004/08/02 18:16
-	359	((313/495-497) or (345/75.2)).CCLS.	US-PGPUB	2004/08/02 18:22
-	1474	((313/495-497) or (345/75.2)).CCLS.	USPAT	2004/08/02 18:29
-	2163	((313/422,495-497) or (345/75.2)).CCLS.	USPAT; US-PGPUB	2004/08/02 18:39
-	36	((313/422,495-497) or (345/75.2)).CCLS.) and (samsung near2 sdi near2 ltd).as.	USPAT; US-PGPUB	2004/08/02 18:29
-	2555	((313/422,495-497) or (345/75.2)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 18:39
-	244	((313/422,495-497) or (345/75.2)).CCLS.) and (mesh grid net network) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 18:40
-	108	((313/422,495-497) or (345/75.2)).CCLS.) and (mesh grid net network) adj electrode and wir\$5 near2 (cathode electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 18:47
-	1	5859508.pn.	USPAT; US-PGPUB	2004/08/02 19:06
-	1	5859508.pn. and (voltage potential volt "V")	USPAT; US-PGPUB	2004/08/02 19:07
-	1	5859508.pn. and (voltage potential volt "V")	USPAT; US-PGPUB	2004/08/02 19:07
-	432	(313/497).CCLS.	USPAT; US-PGPUB	2004/08/03 11:17
-	1	6400073.pn.	USPAT; US-PGPUB	2004/08/03 10:48
-	0	6400073.pn. and (control adj electrode) with (volt\$5 potential bias\$5)	USPAT; US-PGPUB	2004/08/03 10:49
-	0	6400073.pn. and (control adj electrode) with (volt\$5 potential bias\$5 "V")	USPAT; US-PGPUB	2004/08/03 10:55
-	2	((313/497).CCLS.) and electron near2 repulsion	USPAT; US-PGPUB	2004/08/03 11:05
-	185	((313/497).CCLS.) and control\$7 near3 electrode	USPAT; US-PGPUB	2004/08/03 11:14
-	1	6472815.pn. and light adj permeable adj conductive adj film	USPAT; US-PGPUB	2004/08/03 11:13
-	1	6472815.pn.	USPAT; US-PGPUB	2004/08/03 11:13
-	1	6472815.pn. and (light adj permeable adj conductive adj film "14")	USPAT; US-PGPUB	2004/08/03 11:13
-	48	((313/497).CCLS.) and vacuum adj fluorescent adj display	USPAT; US-PGPUB	2004/08/03 11:14
-	16	((313/497).CCLS.) and (vacuum adj fluorescent adj display vfd).ab,ti,clm.	USPAT; US-PGPUB	2004/08/03 11:17
-	2167	((313/422,495-497) or (345/75.2)).CCLS.	USPAT; US-PGPUB	2004/08/03 11:17
-	2559	((313/422,495-497) or (345/75.2)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:17
-	37	((313/422,495-497) or (345/75.2)).CCLS.) and (vacuum adj fluorescent adj display vfd).ab,ti,clm.	USPAT; US-PGPUB	2004/08/03 11:20
-	1	4302706.pn.	USPAT; US-PGPUB	2004/08/03 11:20
-	1	4302706.pn. and (volt\$6 potential bias\$5 "V")	USPAT; US-PGPUB	2004/08/03 11:40

-	1	5055744.pn.	USPAT; US-PGPUB	2004/08/03 13:33
-	1	5055744.pn. and filamentary adj cathode with (volt\$5 potential bias\$4 "V")	USPAT; US-PGPUB	2004/08/03 13:38
-	1	5055744.pn. and (diffusion filamentary cathode) with (volt\$5 potential bias\$4 "V")	USPAT; US-PGPUB	2004/08/03 13:55
-	1	4595862.pn.	USPAT; US-PGPUB	2004/08/03 13:55